


AO3407A
P-Channel Enhancement Mode Field Effect Transistor
General Description

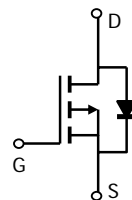
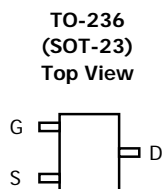
The AO3407A/L uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use as a load switch or in PWM applications. AO3407A and AO3407AL are electrically identical.

- RoHS Compliant
- AO3407AL is Halogen Free

Features

- V_{DS} (V) = -30V
- I_D = -4.3A (V_{GS} = -10V)
- $R_{DS(ON)}$ < 48m Ω (V_{GS} = -10V)
- $R_{DS(ON)}$ < 78m Ω (V_{GS} = -4.5V)

R_g, C_{iss}, C_{oss}, C_{rss} Tested


Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{A,F}	I_D	$T_A=25^\circ\text{C}$	-4.3
		$T_A=70^\circ\text{C}$	-3.5
Pulsed Drain Current ^B	I_{DM}	-20	A
Power Dissipation ^A	P_D	$T_A=25^\circ\text{C}$	1.4
		$T_A=70^\circ\text{C}$	0.9
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^{AF}	$R_{\theta JA}$	$t \leq 10\text{s}$	70	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	100	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	63	80	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-30\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.5	-2	-2.5	V	
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$, $V_{DS}=-5\text{V}$	-30			A	
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-4.3\text{A}$ $T_J=125^\circ\text{C}$		39	48	m Ω	
		$V_{GS}=-4.5\text{V}$, $I_D=-3\text{A}$		61	78		
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-4.3\text{A}$		11		S	
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.78	-1	V	
I_S	Maximum Body-Diode Continuous Current				-2	A	
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$		668	830	pF	
C_{oss}	Output Capacitance				126		pF
C_{rss}	Reverse Transfer Capacitance				92		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		6	9	Ω	
SWITCHING PARAMETERS							
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $I_D=-4.3\text{A}$		12.7	16	nC	
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			6.4		nC	
Q_{gs}	Gate Source Charge			2		nC	
Q_{gd}	Gate Drain Charge			4		nC	
$t_{D(on)}$	Turn-On Delay Time			7.7		ns	
t_r	Turn-On Rise Time	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $R_L=3.5\Omega$, $R_{GEN}=3\Omega$		6.8		ns	
$t_{D(off)}$	Turn-Off Delay Time			20		ns	
t_f	Turn-Off Fall Time			10		ns	
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-4.3\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		22	30	ns	
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-4.3\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		15		nC	

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $< 300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

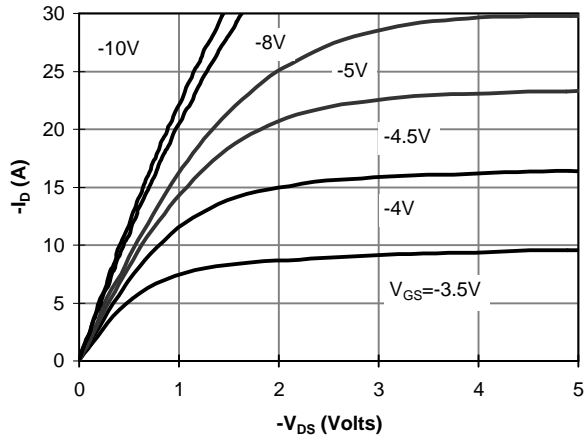


Figure 1: On-Region Characteristics

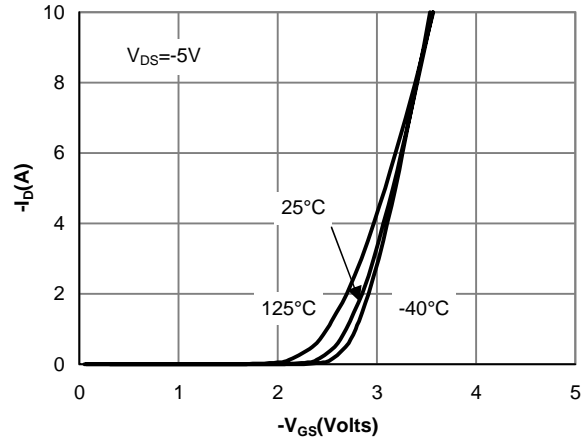


Figure 2: Transfer Characteristics

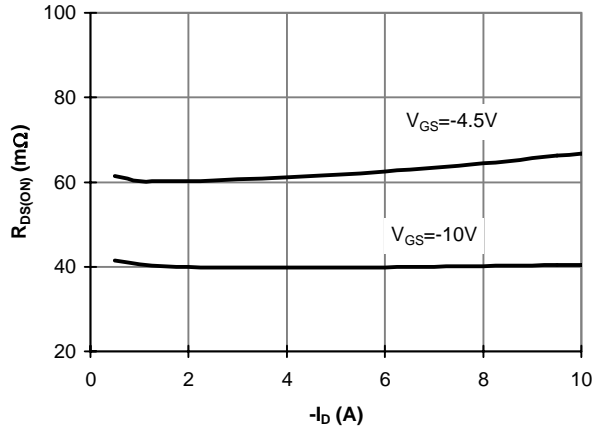


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

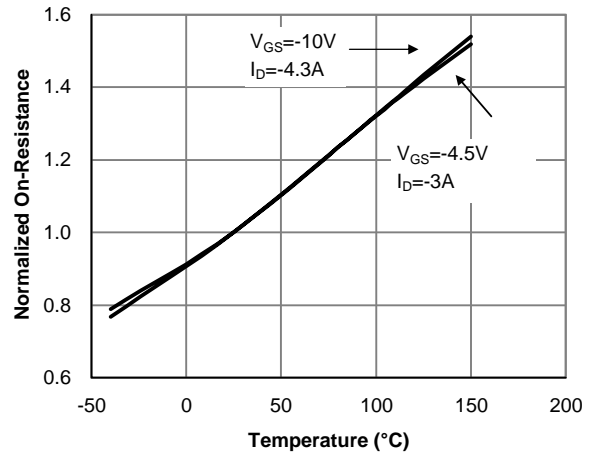


Figure 4: On-Resistance vs. Junction Temperature

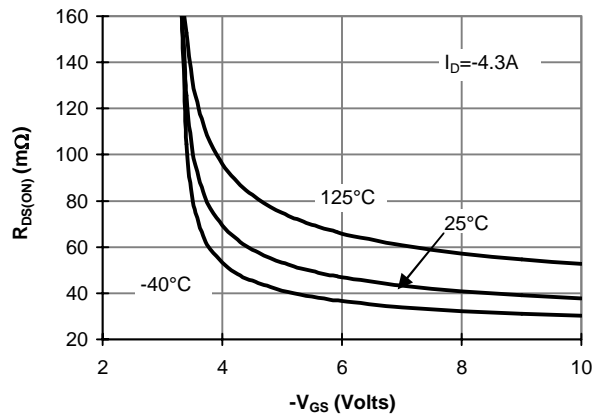


Figure 5: On-Resistance vs. Gate-Source Voltage

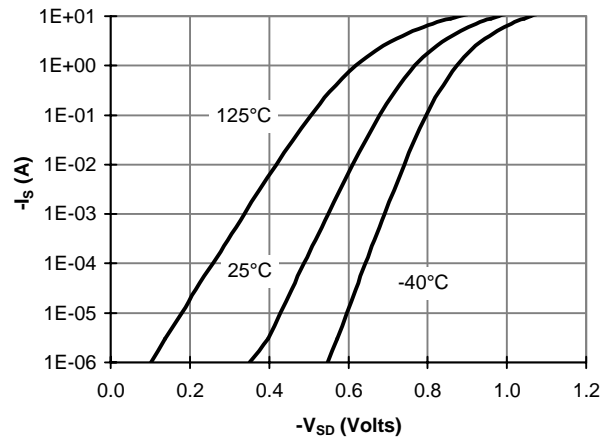


Figure 6: Body-Diode Characteristics

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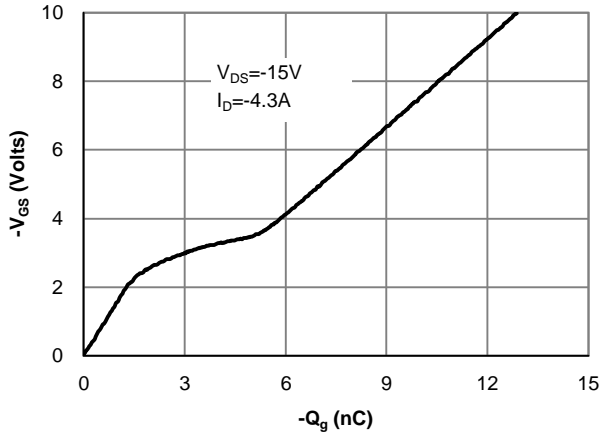


Figure 7: Gate-Charge Characteristics

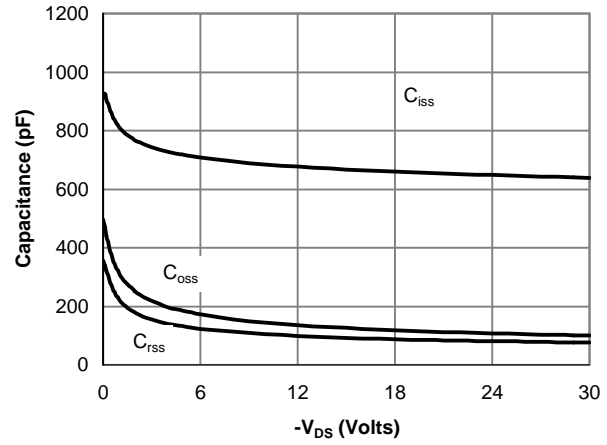


Figure 8: Capacitance Characteristics

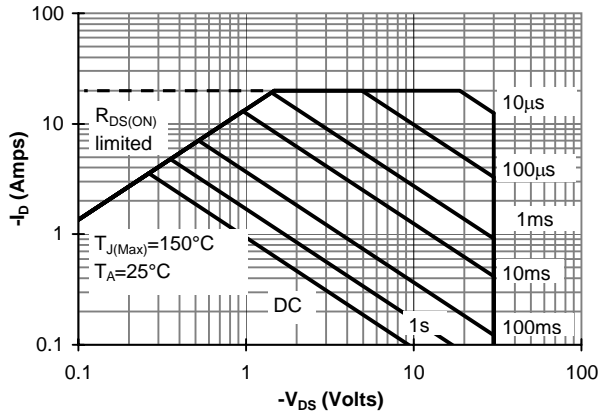


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

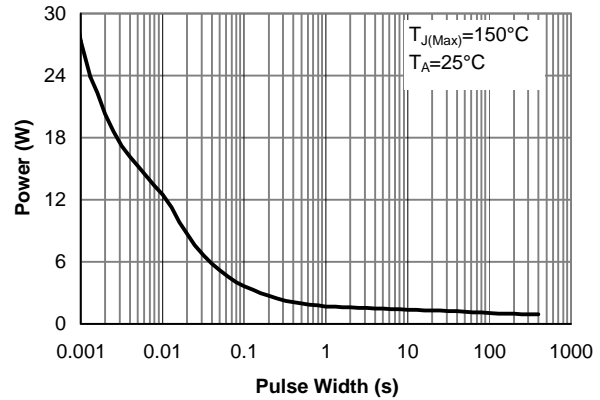


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

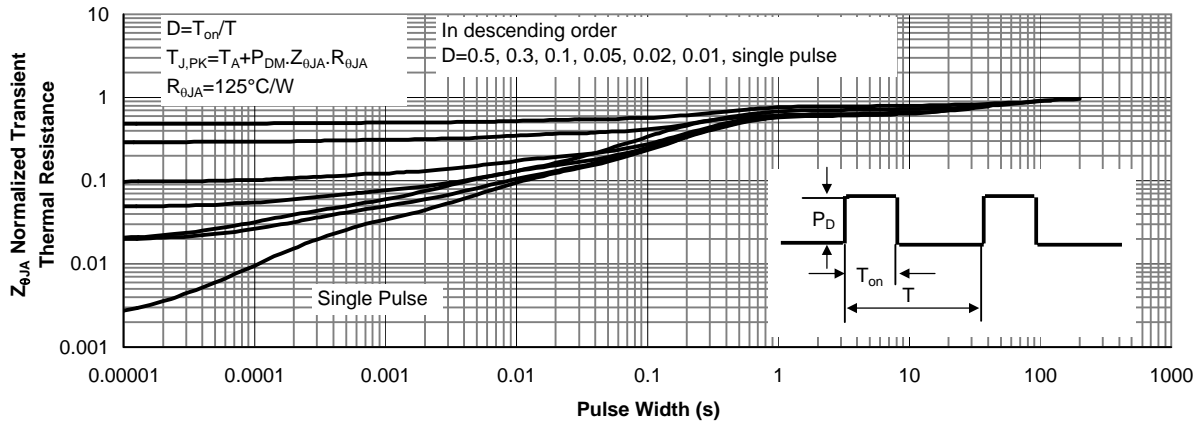


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)